



www.hoyuan.com
sales@hoyuan.com

I

Growing Method
Dopant/Model
Oxygen Content
Carbon Content
Dislocation Density
Crystal Orientation

II

Resistivity
Minority Carrier Lifetime

III

Wafer Model
Geometry
Chamfered Edge Shape
Wafer Side Length
Wafer Diagonal
Chamfered Edge Length
Chord Length
Right Angle
Thickness
Total Thinckness Variation
Saw Marks
Warpage
Slicing Method

Schematic Diagram Of Wafer Dimension

